

**In the Specification:**

Please replace paragraph [0010] with the following paragraph:

-- [0010] Referring to Fig. 2d, an etching process is performed using the photoresist pattern 41 as a mask to remove some part(s) of the first sacrificial layer 39 until the polysilicon layer 37 is exposed through the photoresist pattern 41. At the same time, polymers generated from the etching of the first sacrificial layer 39 are attached to the sidewalls of the etched first sacrificial layer 39 to form polymer layers 43. The polymer layers 43 are used as a second sacrificial layer. Here, the polymer layers 43 are formed so that the space between the adjacent polymer layers 43 is preferably between ~~300Å and 1200Å~~ 300 Å and 1200 Å.--.